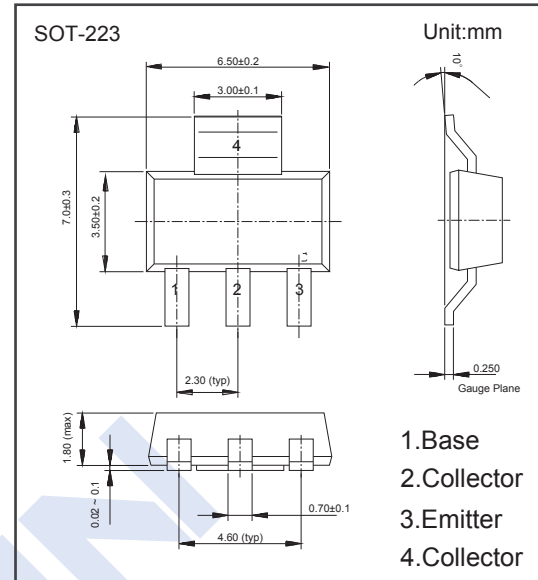
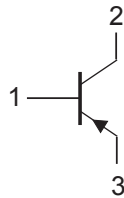


PNP Transistors 2KB4016

■ Features

- High current (max. 1 A)
- Low voltage (max. 20 V)



■ Absolute Maximum Ratings Ta = 25°C

| Parameter | Symbol | Rating | Unit |
|---|------------------|------------|------|
| Collector - Base Voltage | V _{CB0} | -32 | V |
| Collector - Emitter Voltage | V _{CE0} | -20 | |
| Emitter - Base Voltage | V _{EB0} | -5 | |
| Collector Current - Continuous | I _C | -1 | A |
| Collector Current - Pulse | I _{CP} | -2 | |
| Base Current - Pulse | I _{BP} | -0.2 | |
| Collector Power Dissipation | P _C | 1.35 | W |
| Thermal Resistance from Junction to Ambient | R _{θJA} | 91 | °C/W |
| Thermal Resistance from Junction to Soldering Point | R _{θJS} | 10 | |
| Junction Temperature | T _J | 150 | °C |
| Storage Temperature range | T _{stg} | -65 to 150 | |

PNP Transistors 2KB4016

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|--------------------------------------|---------------|--|-----|-------|------|---------------|
| Collector- base breakdown voltage | V_{CB0} | $I_C = -100 \mu\text{A}, I_E = 0$ | -32 | | | V |
| Collector- emitter breakdown voltage | V_{CE0} | $I_C = -1 \text{ mA}, I_B = 0$ | -20 | | | |
| Emitter - base breakdown voltage | V_{EB0} | $I_E = -100 \mu\text{A}, I_C = 0$ | -5 | | | |
| Collector-base cut-off current | I_{CBO} | $V_{CB} = -25 \text{ V}, I_E = 0$ | | | -100 | nA |
| | | $V_{CB} = -25 \text{ V}, I_E = 0, T_J = 150^\circ\text{C}$ | | | -10 | μA |
| Emitter cut-off current | I_{EBO} | $V_{EB} = -5 \text{ V}, I_C = 0$ | | | -100 | nA |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | $I_C = -1 \text{ A}, I_B = -100 \text{ mA}$ | | | -0.5 | V |
| Base - emitter saturation voltage | $V_{BE(sat)}$ | $I_C = -1 \text{ A}, I_B = -100 \text{ mA}$ | | | -1.2 | |
| Base - emitter voltage | V_{BE} | $V_{CE} = -10 \text{ V}, I_C = -5 \text{ mA}$ | | -0.62 | | |
| | | $V_{CE} = -1 \text{ V}, I_C = -1 \text{ A}$ | | | -1 | |
| DC current gain | h_{FE} | $V_{CE} = -10 \text{ V}, I_C = -5 \text{ mA}$ | 50 | | | |
| | | $V_{CE} = -1 \text{ V}, I_C = -500 \text{ mA}$ | 100 | | 250 | |
| | | $V_{CE} = -1 \text{ V}, I_C = -1 \text{ A}$ | 60 | | | |
| Collector capacitance | C_{ob} | $V_{CB} = -5 \text{ V}, I_E = I_C = 0, f = 1 \text{ MHz}$ | | 48 | | pF |
| Transition frequency | f_t | $V_{CE} = -5 \text{ V}, I_C = -10 \text{ mA}, f = 100 \text{ MHz}$ | 40 | | | MHz |

■ Marking

| | |
|---------|-----|
| Marking | 2KD |
|---------|-----|

■ Typical Characteristics

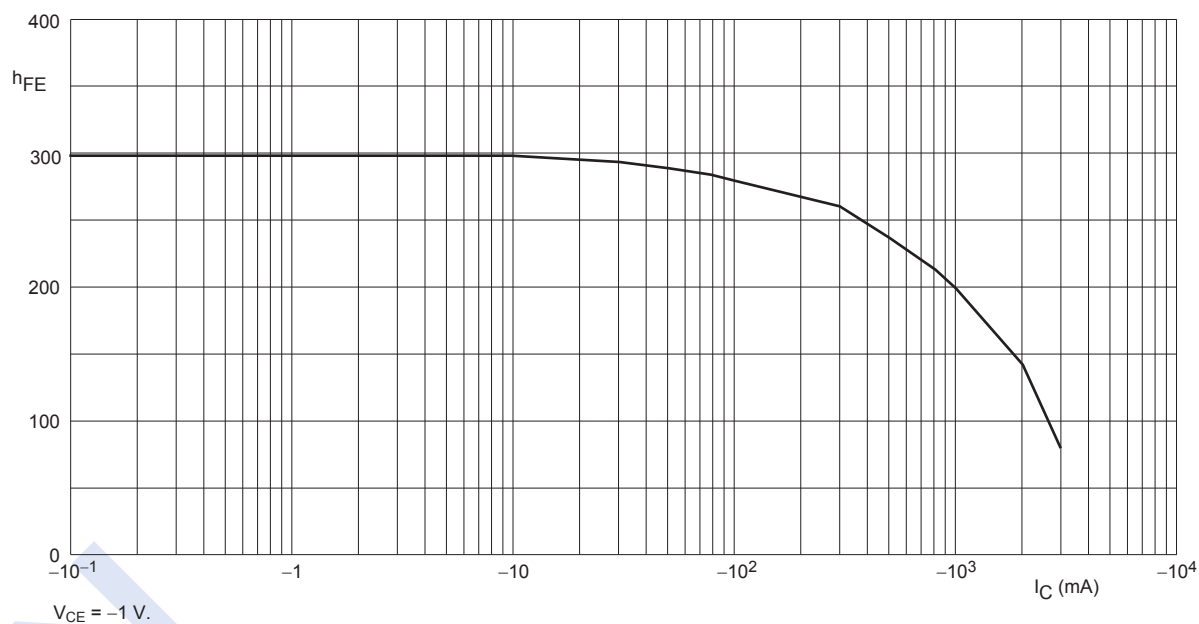


Fig.1 DC current gain; typical values.